



Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 250270US2SDIV		SERIAL NO. 10/798,571	
LIST OF REFERENCES CITED BY APPLICANT				APPLICANT Minoru AMANO, et al.			
				FILING DATE March 12, 2004		GROUP	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA						
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FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES NO		
	AO						
	AP						
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	AR						
	AS						
	AT						
	AU						
	AV						
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)							
<i>MA</i>	AW	R. SCHEUERLEIN, et al., IEEE International Solid-State Circuits Conference, pages 128-129, "TA 7.2 A 10NS READ AND WRITE NON-VOLATILE MEMORY ARRAY USING A MAGNETIC TUNNEL JUNCTION AND FET SWITCH IN EACH CELL", 2000					
<i>MA</i>	AX	M. SATO, et al., IEEE Transactions on Magnetics, vol. 33, no. 5, pages 3553-3555, "SPIN-VALVE-LIKE PROPERTIES AND ANNEALING EFFECT IN FERROMAGNETIC TUNNEL JUNCTIONS", September 1997					
<i>MA</i>	AY	M. SATO, et al., Jpn. J. Appl. Phys., vol. 36, part 2, no. 2B, pages L200-L201, "SPIN-VALVE-LIKE PROPERTIES OF FERROMAGNETIC TUNNEL JUNCTIONS", February 15, 1997					
<i>MA</i>	AZ	K. INOMATA, et al., Jpn. J. Appl. Phys., vol. 36, part 2, no. 10B, pages L1380-L1383, "SPIN-DEPENDENT TUNNELING BETWEEN A SOFT FERROMAGNETIC LAYER AND HARD MAGNETIC NANOSIZE PARTICLES", October 15, 1997				<input type="checkbox"/> Additional References sheet(s) attached	
Examiner <i>M. Makinouchi</i>					Date Considered <i>11/15/04</i>		
*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							